

L Number	Hits	Search Text	DB	Time stamp
2	13	20030107465.pn. 20030022102.pn. 20020197834.pn. 6465742.pn. 20020004180.pn. 6565764.pn. 6709806.pn.	USPAT; US-PGPUB; DERWENT	2004/06/24 09:08
3	6	jp-07207450-\$.did. jp-11025755-\$.did. jp-10149722-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/24 09:14
4	1	2001jp-0170018.ap,prai. 2001jp-0295461.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/24 09:35
5	4	4895756.pn. 5819858.pn. 6504685.pn. 20020157862.pn.	USPAT; US-PGPUB	2004/06/24 10:30
13	7	ASAKAWA-KOJI and HOTTA-YASUYUKI and MATAKE-SHIGERU and HIRAOKA-TOSHIRO	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/24 11:34
14	16	5731073.uref. 5910354.uref.	USPAT; US-PGPUB	2004/06/24 11:35
15	16	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))) and (expos\$4 with beam)	USPAT; US-PGPUB	2004/06/24 11:39
16	0	6649516.URPN.	USPAT	2004/06/24 11:42
17	363	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))) and (via feedthrough throughhole wiring interconnect trace)	USPAT; US-PGPUB	2004/06/24 11:43
18	14	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))) and (via feedthrough throughhole wiring interconnect trace)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 12:09
19	22	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))) and (438/638.ccls. 29/829.ccls. 29/846.ccls. 29/880.ccls. 174/262.ccls. 200/264.ccls. 361/748.ccls.)	USPAT; US-PGPUB	2004/06/24 12:12
20	261	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))) and (via feedthrough throughhole) and (wiring interconnect trace)	USPAT; US-PGPUB	2004/06/24 12:24
21	280	(438/638.ccls. 29/829.ccls. 29/846.ccls. 29/880.ccls. 174/262.ccls. 200/264.ccls. 361/748.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4)))	USPAT; US-PGPUB	2004/06/24 13:21
22	0	6608757.URPN.	USPAT	2004/06/24 13:11
23	6754	257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.	USPAT; US-PGPUB	2004/06/24 13:20
24	292	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4)))	USPAT; US-PGPUB	2004/06/24 16:32
25	40	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and ((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregn\$4))	USPAT; US-PGPUB	2004/06/24 13:22

26	90	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls. 200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and (mask photomask)	USPAT; US-PGPUB	2004/06/24 13:28
27	14	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) same (mask photomask)	USPAT; US-PGPUB	2004/06/24 14:42
28	174	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) and (mask photomask)	USPAT; US-PGPUB	2004/06/24 15:57
29	446	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:56
30	10	((porous pore void) with (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) with (infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 15:59
31	292	((porous pore void) with (insulator material substrate dielectric semiconductor)) same (conduct\$4 metal infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 16:00
32	234	((porous pore void) with (insulator material substrate dielectric semiconductor) with (conduct\$4 metal infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 16:00
33	92	((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same (conduct\$4 metal infiltrat\$4 impregnat\$4)) and (mask photomask)	EPO; JPO; DERWENT; IBM_TDB	2004/06/24 16:01
34	39	430/5.ccls. and (((porous pore void) near2 (insulator material substrate dielectric semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4)))	USPAT; US-PGPUB	2004/06/24 16:32